

Docket No.: M4065.0210/P210-A

(PATENT)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Yang et al.

Application No.: 10/002,176

Filed: December 5, 2001

For: IMPROVED MEMORY CELL CAPACITOR

STRUCTURE AND METHOD OF

**FORMATION** 

Group Art Unit: 2814

Examiner: Vikki H. Trinh

**AMENDMENT** 

Commissioner for Patents Washington, DC 20231

Dear Sir:

AMENDMENT

Soner for Patents
on, DC 20231

This paper is in response to the Office Action dated January 2, 2003. Please above-captioned U.S. Patent application as follows: amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please rewrite claim 32 as follows:

32. (amended) A method of forming a capacitor in a semiconductor device, said method comprising:

forming a bottom conducting layer;

forming a dielectric layer formed over the bottom conducting layer;

forming a top conducting layer over the dielectric layer; and



## AMENDMENT TRANSMITTAL LETTER

Docket No.

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10/002,176		December 5, 2001		Vikki H. Trinh		2814
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